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II. CLAIM AMENDMENTS

1. (Currently Amended) A method of growing semiconductor epitaxial layers on a substrate in a chamber, said method comprising ~~the steps of~~:

providing a substrate,

providing a first growth solution, and

(i) exposing the substrate to the first growth solution, the growth solution being under a supersaturated condition such that a first epitaxial layer grows on the surface of the substrate; and

(ii) compositionally grading the first epitaxial layer by varying the pressure in the chamber to change the degree of supersaturation of the first growth solution during epitaxial growth to affect the growth of the first epitaxial layer.

2. (Previously Presented) A method according to claim 1, further comprising:

providing the first growth solution and the substrate at atmospheric pressure,

heating said growth solution to a temperature above its saturation temperature,